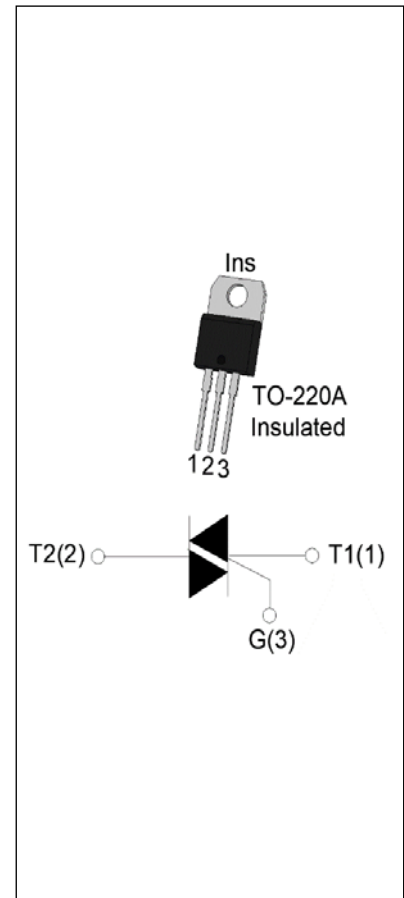


JST06A-800TW 6A TRIAC

Rev.A.1.1

DESCRIPTION:

The JST06A-800TW triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. JST06A-800TW snubberless triac is especially recommended for use on inductive loads. It can be driven directly through the MCU I/O port. By using an internal ceramic pad, JST06A-800TW provides a rated insulation voltage of 2500 VRMS, complying with UL standards (File ref: E252906). Package TO-220A is RoHS compliant.


MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	6	A
V_{DRM}/V_{RRM}	800	V
$I_{GT\ I/II/III}$	5/5/5	mA

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	°C
Operating junction temperature range	T_j	-40-125	°C
Repetitive peak off-state voltage ($T_j=25^{\circ}C$)	V_{DRM}	800	V
Repetitive peak reverse voltage ($T_j=25^{\circ}C$)	V_{RRM}	800	V
RMS on-state current ($T_c \leq 100^{\circ}C$)	$I_{T(RMS)}$	6	A
Non repetitive surge peak on-state current (full cycle , $t_p=20ms$, $T_j=25^{\circ}C$)	I_{TSM}	65	A
Non repetitive surge peak on-state current (full cycle , $t_p=16.6ms$, $T_j=25^{\circ}C$)		72	
I^2t value for fusing ($t_p=10ms$, $T_j=25^{\circ}C$)	I^2t	21	A^2s
Critical rate of rise of on-state current ($I_G=2 \times I_{GT}$, $f=100Hz$, $T_j=125^{\circ}C$)	di/dt	50	$A/\mu s$

Peak gate current ($t_p=20\mu s$, $T_j=125^\circ C$)	I_{GM}	4	A
Average gate power dissipation ($T_j=125^\circ C$)	$P_{G(AV)}$	0.5	W
Peak gate power	P_{GM}	10	W
Peak pulse voltage ($T_j=25^\circ C$; non-repetitive, off-state; FIG. 7)	V_{pp}	3.5	kV

ELECTRICAL CHARACTERISTICS ($T_j=25^\circ C$ unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	$V_D=12V$ $R_L=33\Omega$	I - II - III	MAX.	5	mA
V_{GT}		I - II - III	MAX.	1	V
V_{GD}	$V_D=V_{DRM}$ $T_j=125^\circ C$ $R_L=3.3k\Omega$	I - II - III	MIN.	0.2	V
I_L	$I_G=1.2I_{GT}$	I - III	MAX.	10	mA
		II		15	
I_H	$I_T=100mA$		MAX.	10	mA
dV/dt	$V_D=540V$ Gate Open $T_j=125^\circ C$		MIN.	150	V/ μs
$(dI/dt)_c$	$(dV/dt)_c=10V/\mu s$, $T_j=125^\circ C$		MIN.	0.5	A/ms
t_{on}	$I_G=10mA$ $I_A=200mA$ $I_R=20mA$ $T_j=25^\circ C$		TYP.	2	μs
t_{off}				20	

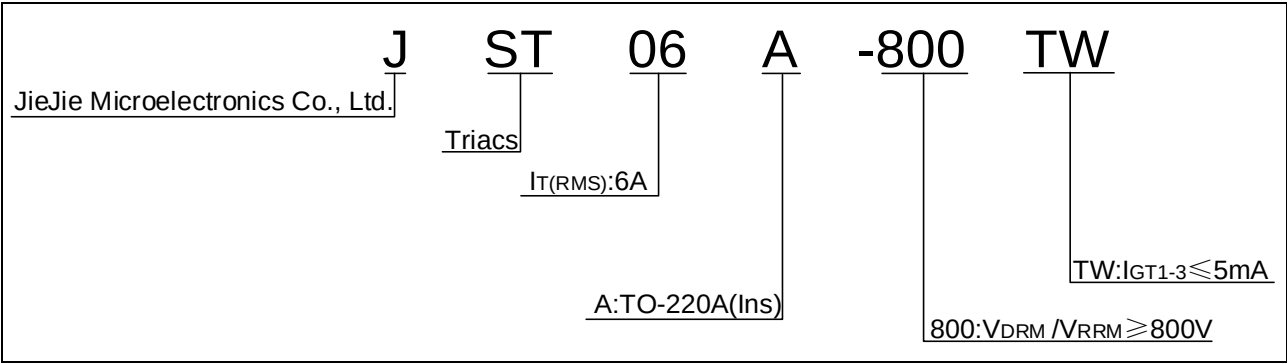
STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	$I_{TM}=8.5A$ $t_p=380\mu s$	$T_j=25^\circ C$	1.5	V
V_{TO}	Threshold voltage	$T_j=125^\circ C$	0.82	V
R_D	Dynamic resistance	$T_j=125^\circ C$	57	m Ω
I_{DRM}	$V_D=V_{DRM}$ $V_R=V_{RRM}$	$T_j=25^\circ C$	5	μA
I_{RRM}		$T_j=125^\circ C$	0.3	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	3	$^\circ C/W$
$R_{th(j-a)}$	junction to ambient (AC)	60	$^\circ C/W$

ORDERING INFORMATION



MARKING

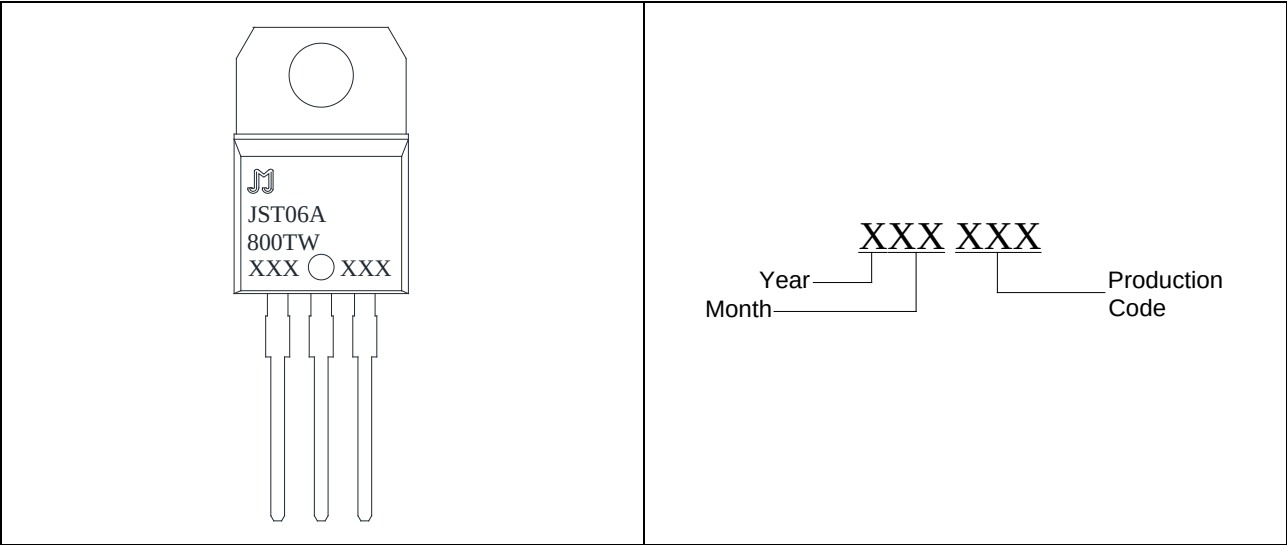


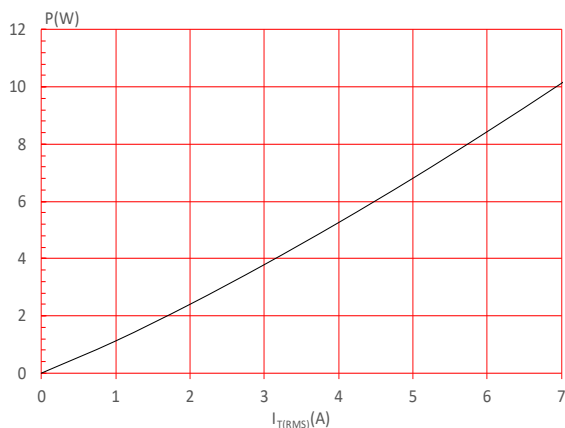
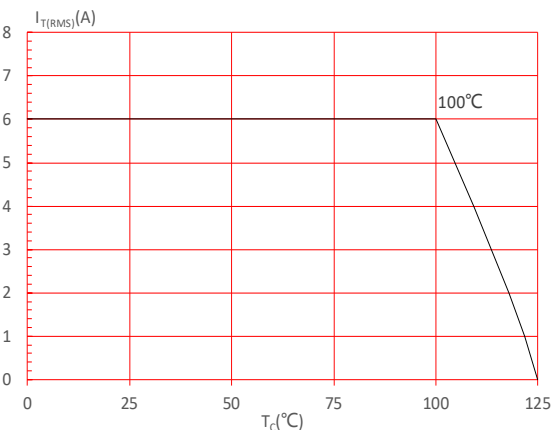
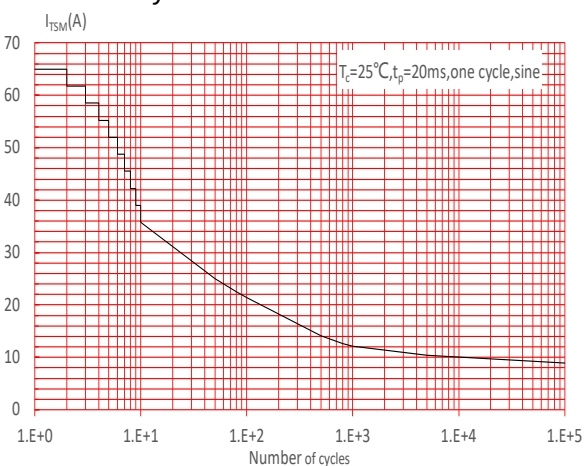
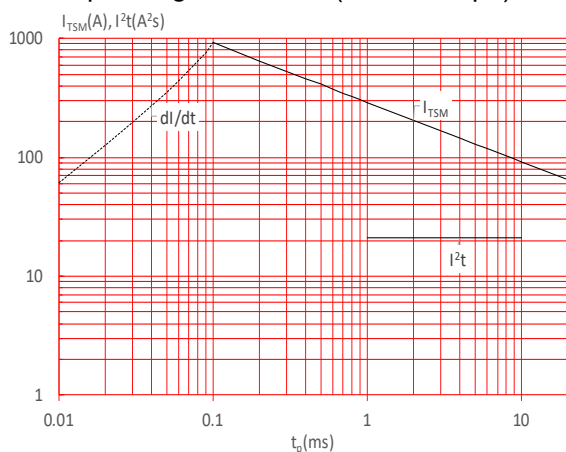
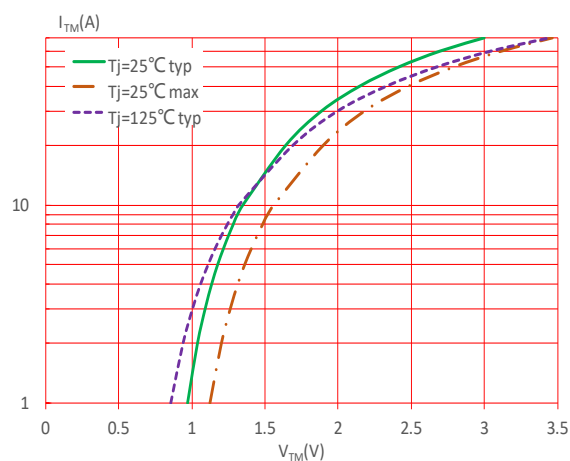
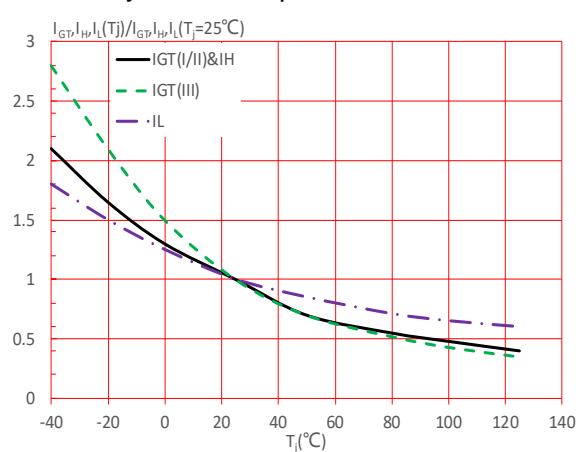
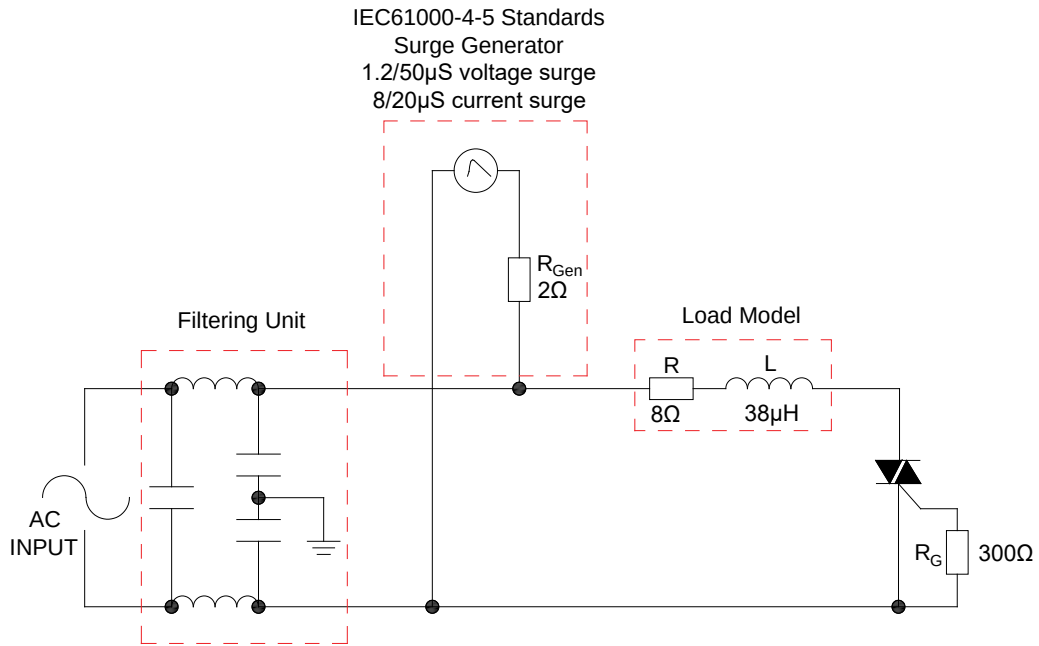
FIG.1: Maximum power dissipation versus RMS on-state current**FIG.2:** RMS on-state current versus case temperature**FIG.3:** Surge peak on-state current versus number of cycles**FIG.5:** Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 20ms$, and corresponding value of I^2t ($di/dt < 50A/\mu s$)**FIG.4:** On-state characteristics**FIG.6:** Relative variations of gate trigger current, holding current and latching current versus junction temperature

FIG.7: Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



LEAD FORMING AND SOLDERING

Refer to the application note “Assembly Instructions for Thyristors in Through-hole Package” released by JieJie Microelectronics

ORDERING INFORMATION

Order code	Voltage $V_{\text{DRM}}/V_{\text{RRM}}$ (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
		I - II - III			
JST06A-800TW	800	5	TO-220A(Ins)	50	Tube

Document Revision History

Date	Revision	Changes
Apr.11, 2023	A.1.0	Last updated
Oct.11, 2025	A.1.1	Revise PACKAGE MECHANICAL DATA

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